

Silicon NPN Power Transistors

2N5466 2N5467

DESCRIPTION

- With TO-3 package
- High-voltage capability
- Fast switching speeds
- Low collector saturation voltage

APPLICATIONS

- They are intended for use in off-line power supplies ,inverter and converter circuits

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a =$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N5466	Open emitter	500	V
		2N5467		700	
V_{CEO}	Collector-emitter voltage		Open base	400	V
V_{EBO}	Emitter-base voltage		Open collector	7	V
I_C	Collector current			3	A
I_{CM}	Collector current-peak			5	A
I_B	Base current			1	A
P_D	Total Power Dissipation		$T_C = 25$	140	W
T_j	Junction temperature			150	
T_{stg}	Storage temperature			-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th j-c}$	Thermal resistance junction to case	1.48	/W

Silicon NPN Power Transistors**2N5466 2N5467****CHARACTERISTICS****T_j=25** unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.2A ; I _B =0	400			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A; I _B =0.4A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2A; I _B =0.4A			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =ratedV _{CB} ; I _E =0			1.0	mA
I _{CEV}	Collector cut-off current	V _{CE} =ratedV _{CE} ; V _{BE(off)} =1.5V T _C =125			1.0 5.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =4V	15		45	
h _{FE-2}	DC current gain	I _C =2A ; V _{CE} =4V	8			
f _T	Transistion frequency	I _C =1A ; V _{CE} =10V; f=1MHz	2.5			MHz

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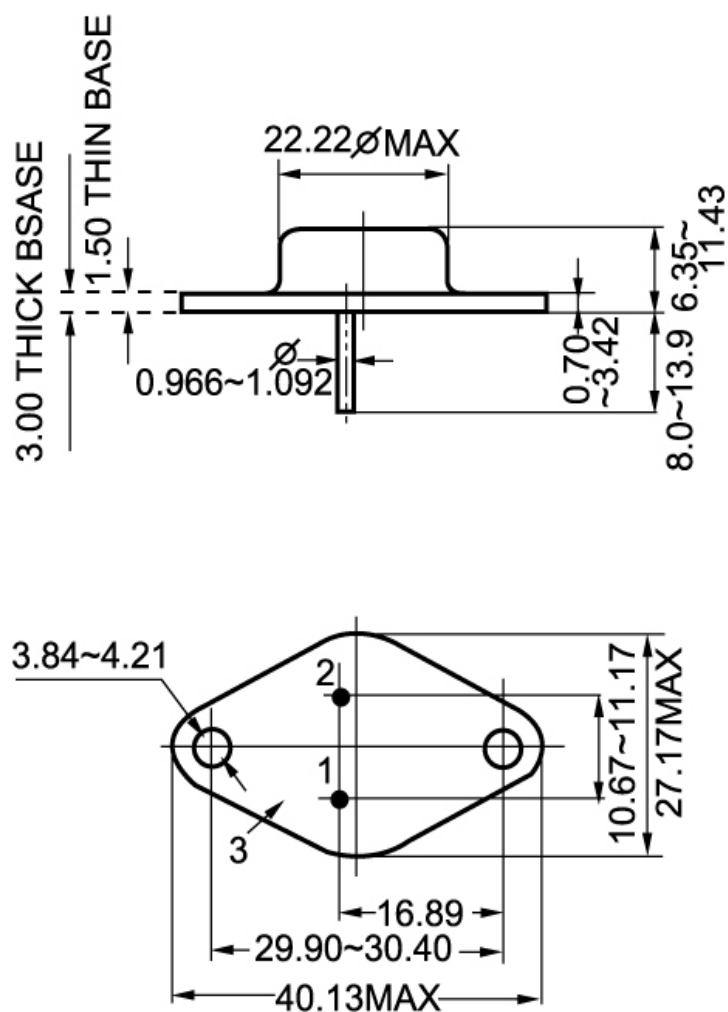


Fig.2 outline dimensions (unindicated tolerance:±0.10mm)